# YJ Planar Schottky Barrier Diode Die Specification

**40V 10A, 84mil, Schottky barrier diode die based on silicon planar process**
**Part No.: PSB084N040SS-280A**

## Main Products Characterstics

## Maximum Ratings

**Rating**

## Static Electrical Characteristics (Ta = 25°C)

| **Parameter** | **Symbol** |
|---|---|
| Reverse breakdown voltage<br>$I_R$ | $V_{BR}$ |
| $I_F =$ 10 A |  |
| ≤ 2% |  |
| Maximum reverse current<br>$V_R = V_{RRM}$<br>≤ 2% | $I_R$ |

Maximum ota513(i)-(ing4(ja8((nc2(t)4(N)-6nnt)]TETBT1 0 0 1 30.34759.71 Tm3()-e(um)-1per6(a8((cur)2ge)]TET EMC Q55211 472.03 31.64 23.28 re W

## Device Schematics and Outline Drawing

| | |
|---|---|
| Die Thickness * | |
| Die Size ** | 84 Mils |
| Top Metal Pad | |
| Active Area | |
| Top Metal | |
| Back Metal | Ag |

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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